

Electronic properties of LaNiInH_x compounds

Ł. Wasyłkiewicz¹, A. Jezierski², and A. Szytuła³

¹*Faculty of Technical Physics, Poznań University of Technology
Nieszawska 13A, 60-965 Poznań, Poland*

²*Institute of Molecular Physics, Polish Academy of Sciences
M. Smoluchowskiego 17, 60-179 Poznań, Poland*

³*M. Smoluchowski Institute of Physics, Jagiellonian University
Reymonta 4, 30-059 Kraków, Poland*

The electronic properties of LaNiInH_x compounds were studied recently [1]. In this work we report the influence of the doped hydrogen on the electronic structure of the LaNiInH_x ($x=0, 1/3, 2/3$ and 1) compounds which crystallize with ZrNiAl-type structure. The electronic properties were calculated by using ASW method [2].

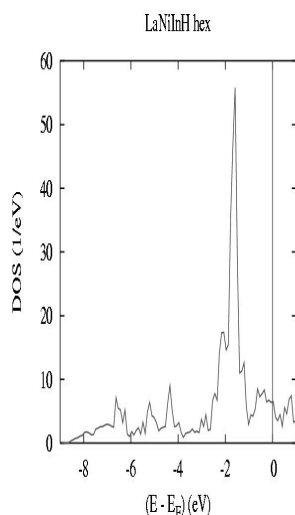


Fig. 1. Total density of states.

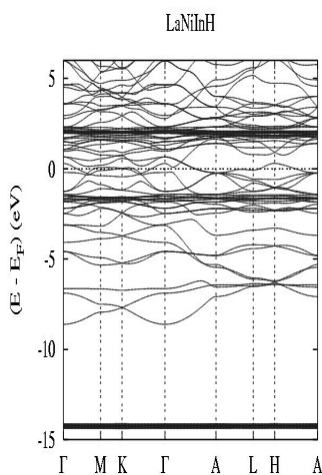


Fig. 2. Band structure.

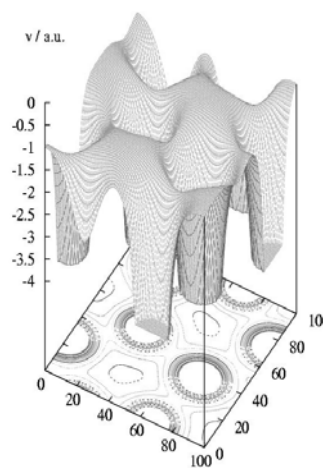


Fig. 3. Charge density.

The hydrogenation does not influence on the crystal structure, however we observe the change of the density of states near the Fermi level, the charge densities and band structure on the position of hydrogen in the unit cell.

[1] A. Jezierski, B. Penc, A. Szytuła, J. Alloys and Compd. **404** (2005) 204

[2] V. Eyert, The Augmented Spherical Wave Method, Lecture Notes in Physics, **719** (2007)

Name of the presenting author (poster session II): Andrzej Jezierski
e-mail address: jeziarsk@ifmpan.poznan.pl
<http://www.ifmpan.poznan.pl>